

## PSMN2R8-40PS

# N-channel TO220 40 V 2.8 mΩ standard level MOSFET 11 February 2013 Product data sheet

### 1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	211	W
T <sub>j</sub>	junction temperature			-55	-	175	°C
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13		-	-	4.5	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; Fig. 13	[2]	-	2.3	2.8	mΩ
Dynamic char	acteristics						
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 20 V;		-	17	-	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 14; Fig. 15		-	71	-	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 40 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	-	407	mJ

- [1] Continuous current rating is limited by package.[2] Measured 3 mm from package.

## **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	704	
3	S	source		G—U: 4
mb	D	mounting base; connected to drain		mbb076 S
			TO-220AB (SOT78)	

### **Ordering information**

Table 3. **Ordering information** 

Type number	Package				
	Name	Description	Version		
PSMN2R8-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

### **Marking**

Table 4. **Marking codes** 

Type number	Marking code
PSMN2R8-40PS	PSMN2R8-40PS

### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 1</u>	[1]	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	[1]	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	797	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	211	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
Is	source current	T <sub>mb</sub> = 25 °C		-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	797	Α
Avalanche	ruggedness	1	-1	-	'	
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_{D}$ = 100 A; $V_{sup}$ ≤ 40 V; unclamped; $R_{GS}$ = 50 Ω		-	407	mJ

[1] Continuous current rating is limited by package.

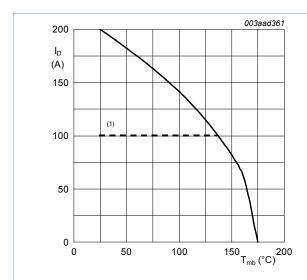


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{\it GS} \geq 10\,V \label{eq:VGS}$$
 (1) Capped at 100 A due to package.

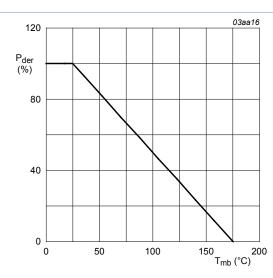


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

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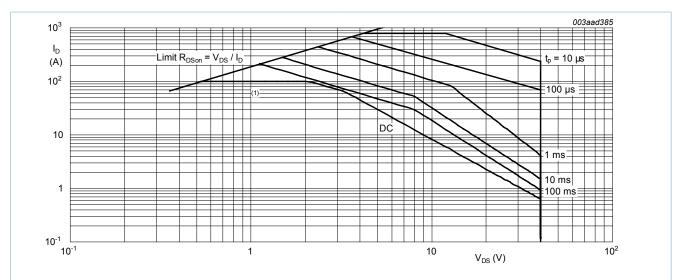


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$  °C;  $I_{DM}$  is a single pulse; (1) Capped at 100 A due to package

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.4	0.7	K/W

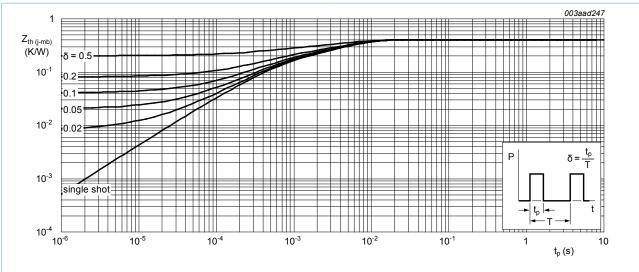


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 10. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
,		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		36	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		40	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10; Fig. 11		-	-	4.6	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11		1	-	-	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; Fig. 10; Fig. 11		2.3	3	4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	0.3	10	μΑ
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C		-	-	150	μΑ
I <sub>GSS</sub> gate leakage current	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	10	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C		-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 100 °C; Fig. 12; Fig. 13		-	-	4.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13		-	-	5.6	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; Fig. 13	[1]	-	2.3	2.8	mΩ
$R_G$	internal gate resistance (AC)	f = 1 MHz		-	0.7	-	Ω
Dynamic ch	aracteristics						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V		-	61	-	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 10 V;		-	71	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 14; Fig. 15		-	21	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge			-	13	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			-	8.5	-	nC
$Q_{GD}$	gate-drain charge			-	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 20 V; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	4.7	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		-	4491	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>		-	937	-	pF

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C <sub>rss</sub>	reverse transfer capacitance			-	464	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 20 V; $R_L$ = 0.8 $\Omega$ ; $V_{GS}$ = 10 V;		-	28	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$		-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	52	-	ns
t <sub>f</sub>	fall time			-	23	-	ns
Source-dra	in diode				'		
$V_{SD}$	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S$ = 40 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V		-	47	-	ns
Q <sub>r</sub>	recovered charge	$I_S$ = 40 A; $dI_S/dt$ = -100 A/ $\mu$ s; $V_{GS}$ = 0 V; $V_{DS}$ = 20 V; $T_j$ = 25 °C		-	61	-	nC

#### [1] Measured 3 mm from package.

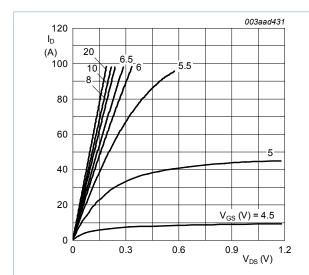


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



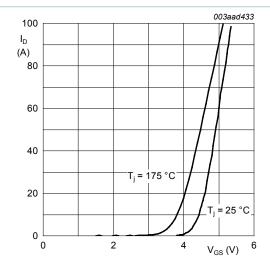


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

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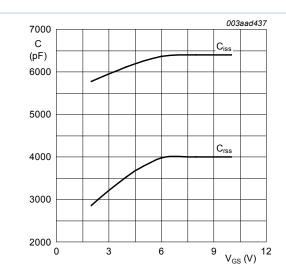


Fig. 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS} = 0V; f = 1MHz$$

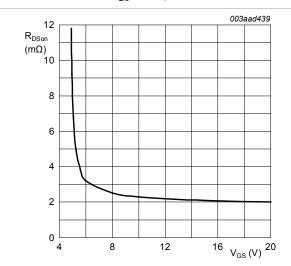


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25\,^{\circ}C; I_D = 25A$$

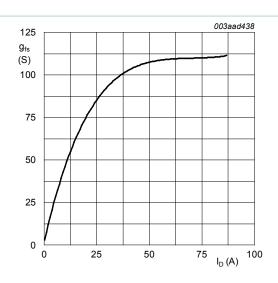


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25\,^{\circ}C; V_{DS} = 15\,V$$

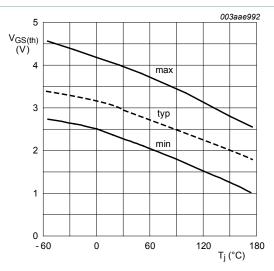


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

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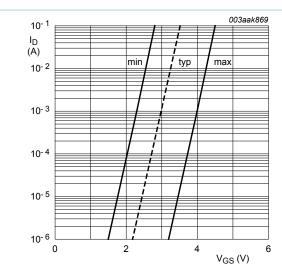


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

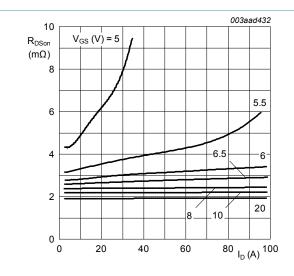


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

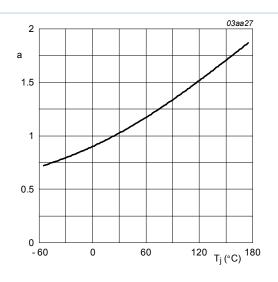


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

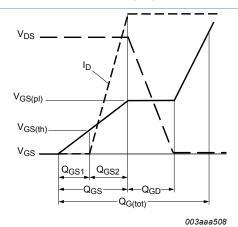


Fig. 14. Gate charge waveform definitions

#### N-channel TO220 40 V 2.8 m $\Omega$ standard level MOSFET

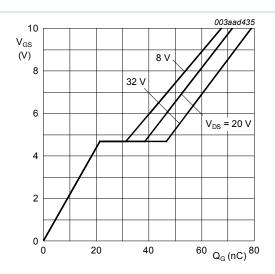


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 10A$$

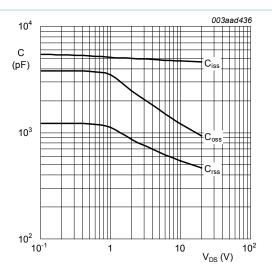


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

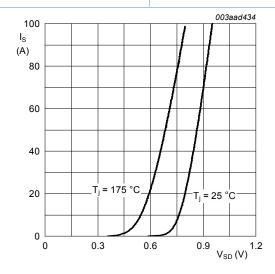
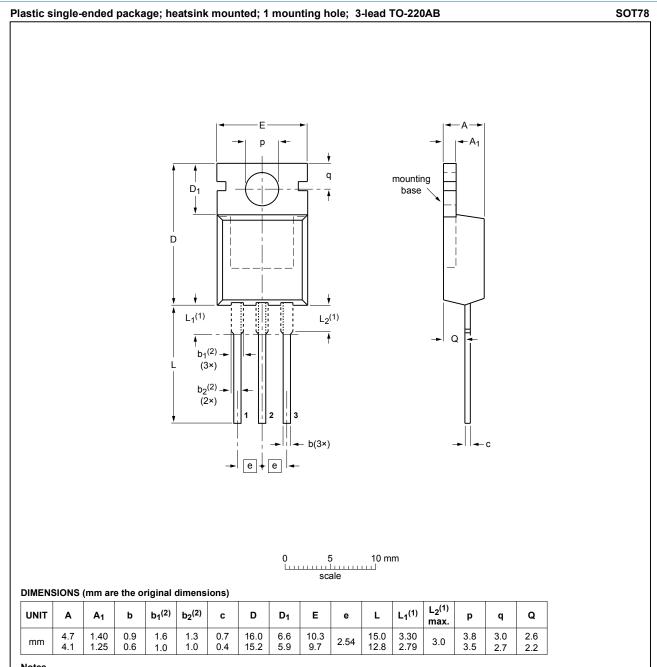


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

### 11. Package outline



- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE	REFERENCES		REFERENCES		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE			
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13			

Fig. 18. Package outline TO-220AB (SOT78)

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